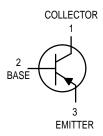
# **Low Noise Transistors PNP Silicon**



#### **MAXIMUM RATINGS**

Rating	Symbol	BC559	BC560	Unit		
Collector-Emitter Voltage	VCEO	-30	-45	Vdc		
Collector-Base Voltage	VCBO	-30	-50	Vdc		
Emitter-Base Voltage	VEBO	-5.0		Vdc		
Collector Current — Continuous	IC	-100		mAdc		
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0		mW mW/°C		
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12				Watt mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C		

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = 0)	BC559 BC560	V(BR)CEO	-30 -45	_ _	_ _	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = -10 μAdc, I <sub>E</sub> = 0)	BC559 BC560	V(BR)CBO	-30 -50			Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = -10 μAdc, I <sub>C</sub> = 0)		V(BR)EBO	-5.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_{E} = 0)$ $(V_{CB} = -30 \text{ Vdc}, I_{E} = 0, T_{A} = +125^{\circ}\text{C})$		ICBO	_ _	_ _	-15 -5.0	nAdc μAdc
Emitter Cutoff Current (V <sub>EB</sub> = -4.0 Vdc, I <sub>C</sub> = 0)		IEBO	_	_	-15	nAdc

## BC559, B, C BC560C



## BC559, B, C BC560C

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS					
DC Current Gain $ (I_{C} = -10 \ \mu Adc, \ V_{CE} = -5.0 \ Vdc) \\ (I_{C} = -2.0 \ mAdc, \ V_{CE} = -5.0 \ Vdc) \\ (I_{C} = -2.0 \ mAdc, \ V_{CE} = -5.0 \ Vdc) \\ BC559B \\ BC559C/560C \\ BC559$	hFE	100 100 180 380 120	150 270 290 500	— 460 800 800	-
Collector-Emitter Saturation Voltage  (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = -0.5 mAdc)  (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = see note 1)  (I <sub>C</sub> = -100 mAdc, I <sub>B</sub> = -5.0 mAdc, see note 2)	VCE(sat)		-0.075 -0.3 -0.25	-0.25 -0.6 	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = -100 mAdc, I <sub>B</sub> = -5.0 mAdc)	V <sub>BE(sat)</sub>	_	-1.1		Vdc
Base–Emitter On Voltage  (I <sub>C</sub> = -10 μAdc, V <sub>CE</sub> = -5.0 Vdc)  (I <sub>C</sub> = -100 μAdc, V <sub>CE</sub> = -5.0 Vdc)  (I <sub>C</sub> = -2.0 mAdc, V <sub>CE</sub> = -5.0 Vdc)  SMALL–SIGNAL CHARACTERISTICS	VBE(on)	  _0.55	-0.52 -0.55 -0.62	  	Vdc
Current – Gain — Bandwidth Product (I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -5.0 Vdc, f = 100 MHz)	fT	_	250	_	MHz
Collector–Base Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cbo</sub>	_	2.5	_	pF
Small–Signal Current Gain (I <sub>C</sub> = -2.0 mAdc, V <sub>CE</sub> = -5.0 V, f = 1.0 kHz) BC559B BC559C/BC560C	h <sub>fe</sub>	240 450	330 600	500 900	_
Noise Figure (I <sub>C</sub> = $-200~\mu$ Adc, V <sub>CE</sub> = $-5.0~V$ dc, R <sub>S</sub> = $2.0~k\Omega$ , f = $1.0~kHz$ ) (I <sub>C</sub> = $-200~\mu$ Adc, V <sub>CE</sub> = $-5.0~V$ dc, R <sub>S</sub> = $100~k\Omega$ , f = $1.0~kHz$ , $\Delta$ f = $200~kHz$ )	NF <sub>1</sub> NF <sub>2</sub>		0.5 —	2.0 10	dB

### NOTES:

<sup>1.</sup> I<sub>B</sub> is value for which I<sub>C</sub> = -11 mA at V<sub>CE</sub> = -1.0 V. 2. Pulse test =  $300 \ \mu s$  – Duty cycle = 2%.

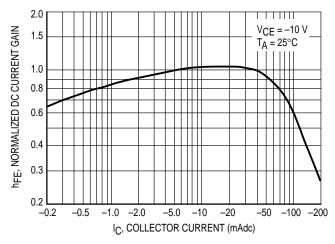


Figure 1. Normalized DC Current Gain

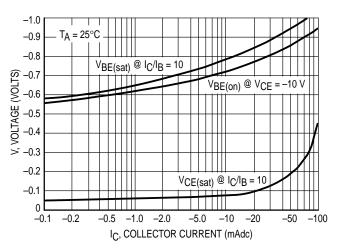


Figure 2. "Saturation" and "On" Voltages

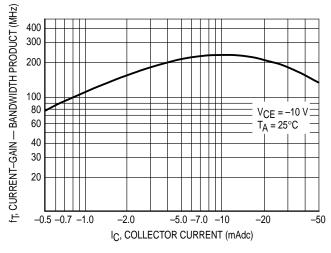


Figure 3. Current-Gain — Bandwidth Product

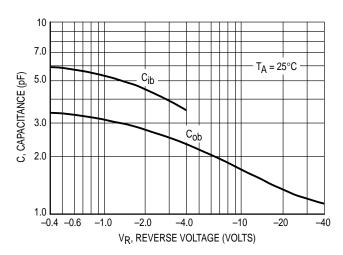


Figure 4. Capacitance

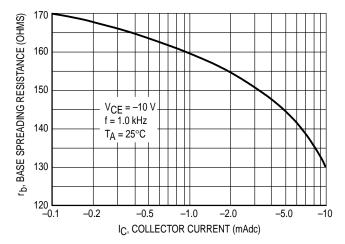
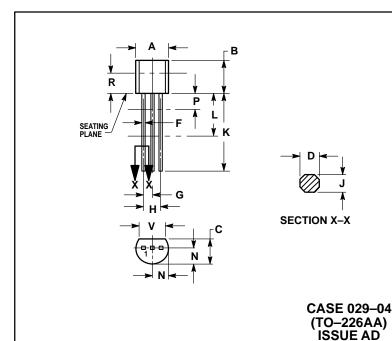


Figure 5. Base Spreading Resistance

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
  DIMENSION D AND J APPLY BETWEEN L AND K
  MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3 43	

STYLE 17:

PIN 1. COLLECTOR

2. BASE

3. EMITTER

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